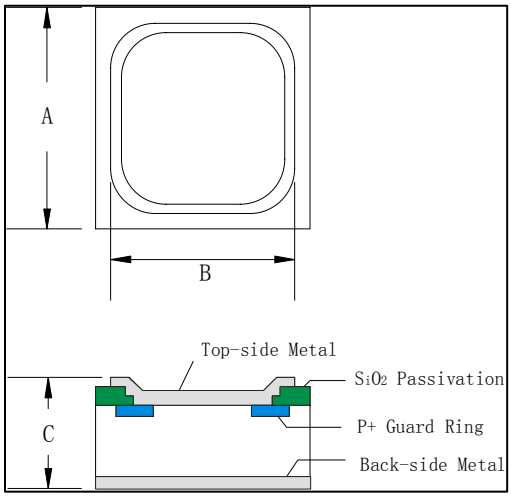
SCHOTTKY DIE SPECIFICATION TYPE: SB1660

General Description: 60 V 16 A (☑Standard ☐Low) VF， (☑Single ☐Dual) Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	60	65	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	16		Amp
Maximum Instantaneous Forward Voltage				
@16 Amperes, Ta=25℃	VF MAX	0.630	0.600	Volt
Maximum Instantaneous Reverse Voltage				
VR= 63 Volt, Ta=25℃	IR MAX	0.400	0.350	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	310		Amp
Operating Junction Temperature	Tj	125		℃
Storage Temperatures	TSTG	-50 to +150		℃

Specification apply to die only. Actual performance may degrade when assembled.
We do not guarantee device performance after assembly.
Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING



DIM	ITEM	μm	Mil
A	Die Size	3124	122.99
B	Top Metal Pad Size	2986	117.56
C	Thickness (Min)	203	8.00
	Thickness (Max)	254	10.00

PS:

(1)Cutting street width is around 50 μm (1.96mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.